



Low Power Sensor Concepts

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- The Silicon Pixel Tracker (SPT):
 - The main driver is **low detector mass**
 - Low mass is enabled by **low detector power**
 - Benefits the forward tracker from the reduced cooling, cables and mechanical structure
 - Could equally well be called “low mass pixel tracker”
 - The concept includes barrel and forward trackers using the same technology
- Low power, low noise, large pixel sensors
 - Large pixels with low noise are challenging in principle
 - Prompt charge collection and efficient data sparsification with high detection efficiency
 - Low average **and** peak power

Low Power Sensor Concept



- Integrating tracker
 - Binary readout - only hit pixels are read out, flagged by in-pixel logic
 - In-pixel electronics should be very power efficient
 - All detector readout
 - Just a source follower in pixel, but has on-chip sparsification
- Rough calculation:
 - 30 Gpixels
 - **1 μ A operating current per pixel @1.8V**
 - 1% duty factor
 - Average power = 540W (but could be lower)
- For the SPT the idea is to make the signal as large as possible
 - Simplifies the in-pixel electronics, gain and power are reduced
 - Electronic noise becomes less of an issue if the signal is very large

How Signal is Usually Detected in HEP



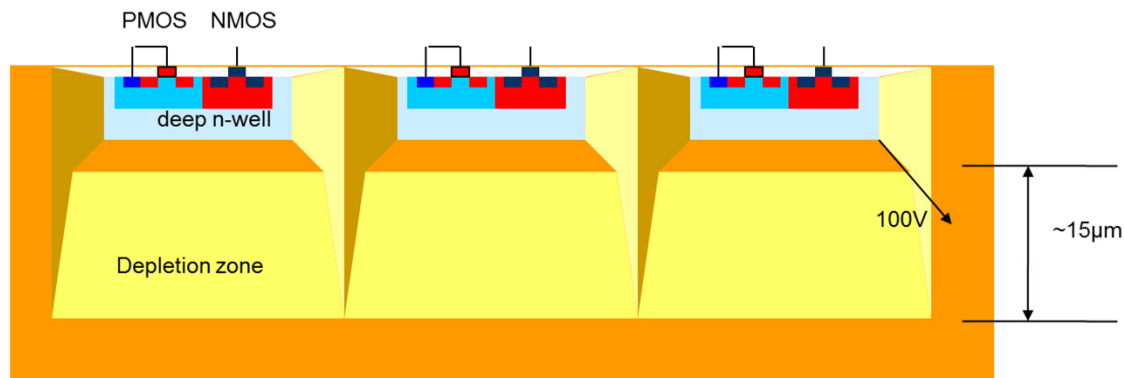
- **Signal is immediately converted to voltage at the place of collection**
 - Microstrips, hybrid pixels, monolithic active pixel sensors
 - The voltage is developed across the capacitance of the collecting element (a diode)
 - $\Delta V = \Delta Q / C$
 - If C is large, ΔV is small -> can increase ΔQ by making the sensor thicker ($\approx 80 \text{ e-}/\mu\text{m}$)
- **Separating the charge collection from the voltage conversion has benefits:**
 - Charge-to-voltage conversion factor (CVF) does not depend on the size of the collecting element
 - The collecting element can be very large, or very small – the choice is yours
 - The sense node must be kept small to generate high voltage from small signal
- **The downside:**
 - Charge transfer from the collecting element to the sense node is required
 - Adds complexity

HV-CMOS for HL-LHC



HV-CMOS sensors – the structure

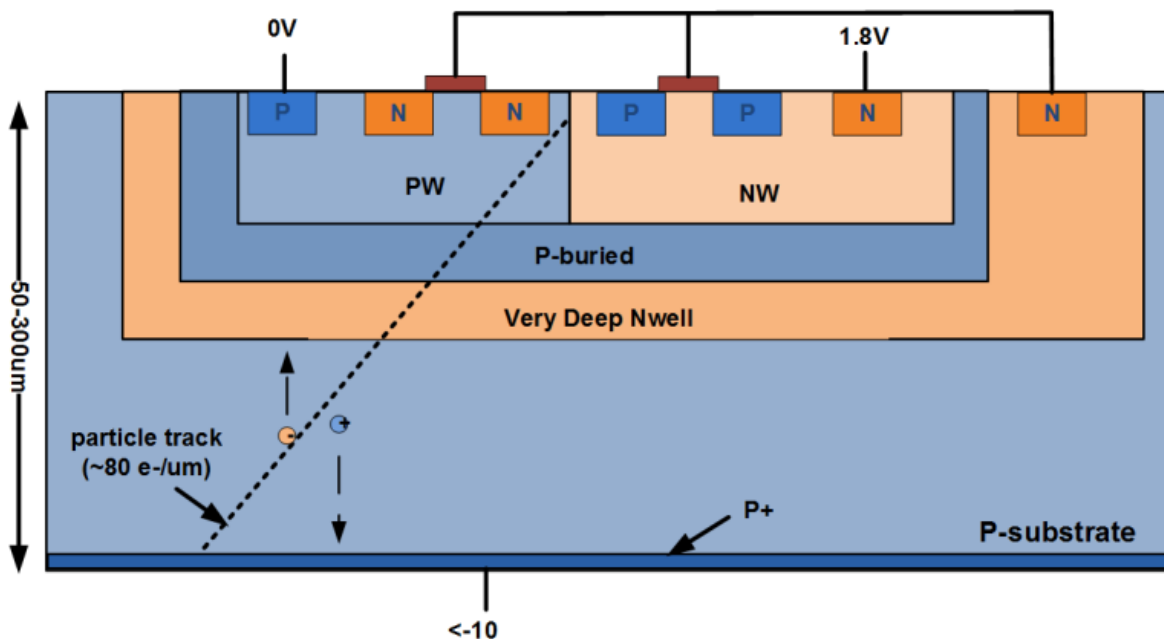
- Example AMS 350nm AMS HV: Typical reverse bias voltage is 60-100 V and the depleted region depth $\sim 15 \mu\text{m}$.
- $20 \Omega\text{cm}$ substrate resistance \rightarrow acceptor density $\sim 10^{15} \text{ cm}^{-3}$.



Ivan Perić, Heidelberg

- The electronics is **inside** the collecting diodes
- Modest depletion due to low resistivity silicon
- Far from ideal, as it stands
 - Large diode capacitance
 - Higher resistivity substrate required to deplete deeper

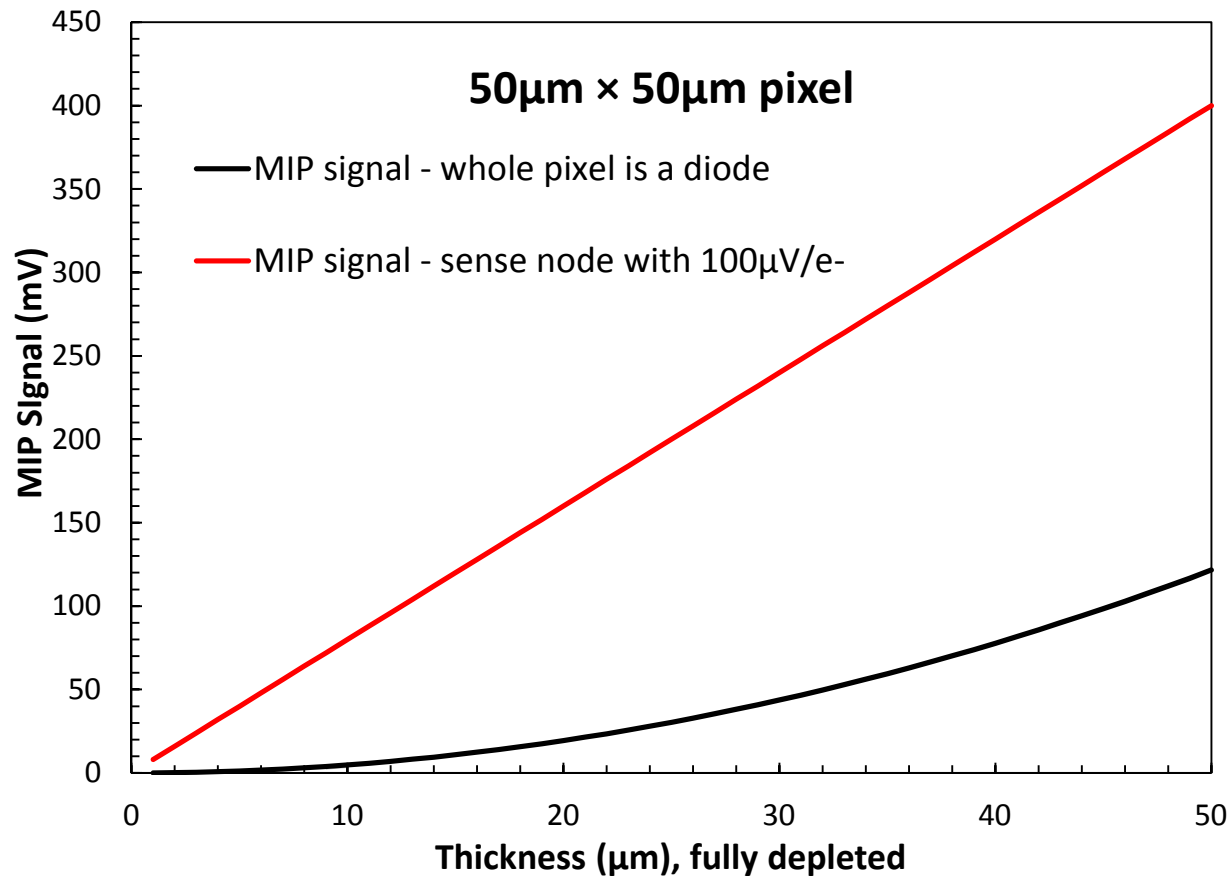
PEGASUS - Depleted MAPS (180nm)



Tomasz Hemperek, Bonn U

- Designed by Strasbourg
- 18 μm thick substrate
- Back-side biased to -20V for full depletion
- 25 μm x 25 μm pixels
- Noise $\approx 15 e^-$
- Will not scale well towards larger pixels

Small Sense Node vs. Large Diode



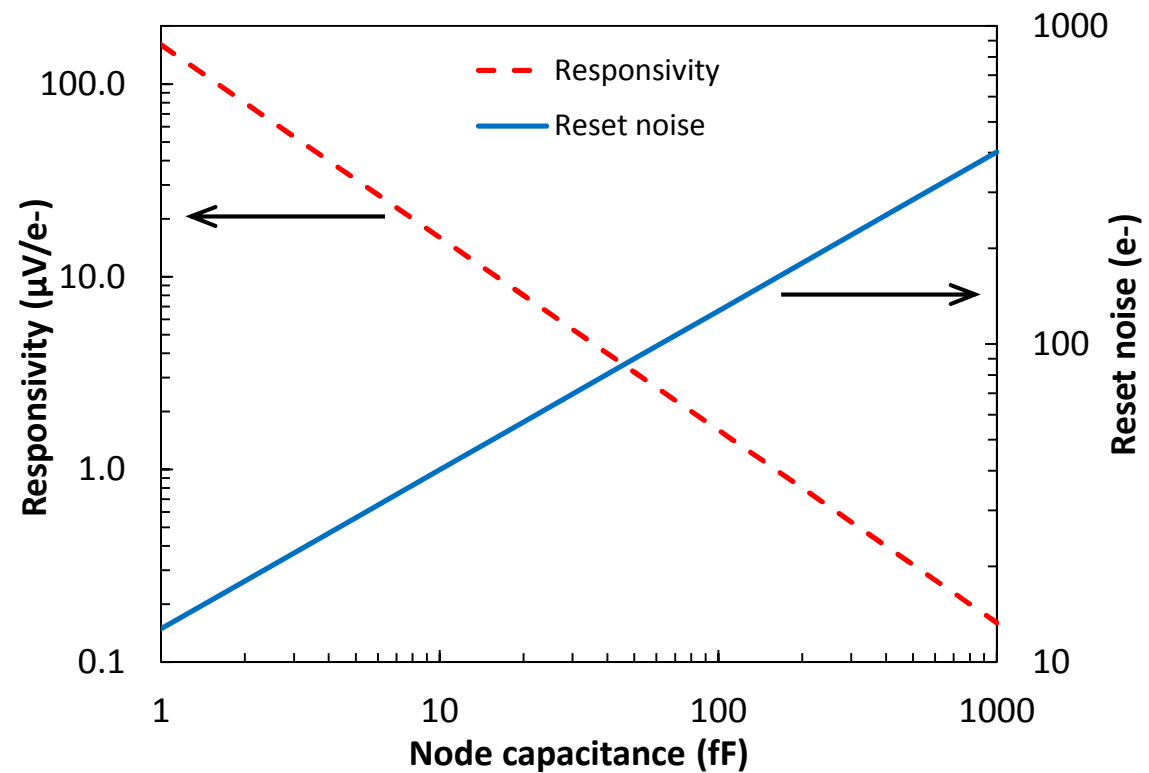
- High sensitivity node offers much higher voltage signal
- Large collecting diodes or multiple small diodes are no match
- Assuming full depletion (reduces diode capacitance)
- Larger signal requires less gain (e.g. $\times 3$ could be fine) and less power
- Low power, noisy electronics could be OK.
- **The equivalent for single photon imaging, but for MIPs**

Reset Noise



$$\text{Reset noise in electrons RMS: } N = \frac{\sqrt{kTC_n}}{q}$$

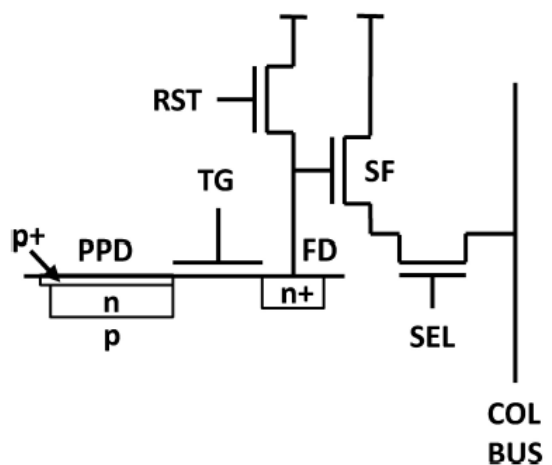
C_n (fF)	Responsivity ($\mu\text{V}/e^-$)	Reset noise (e^-)
1	160	12.72
2	80	17.98
5	32	28.44
10	16	40.21
20	8	56.87
50	3.2	89.92
100	1.6	127.17
200	0.8	179.84
500	0.32	284.36
1000	0.16	402.14



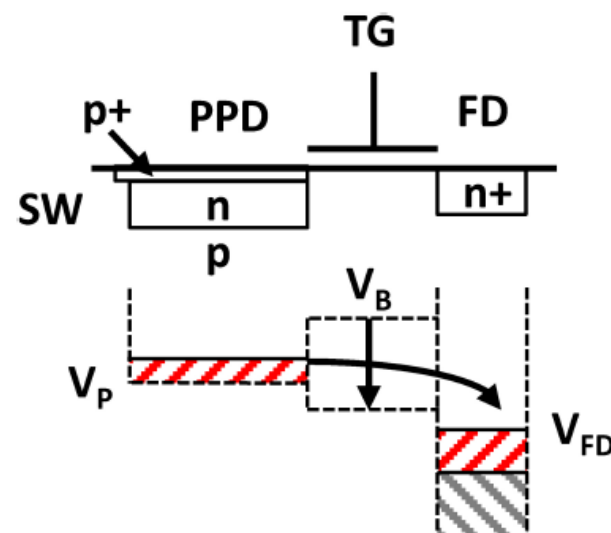
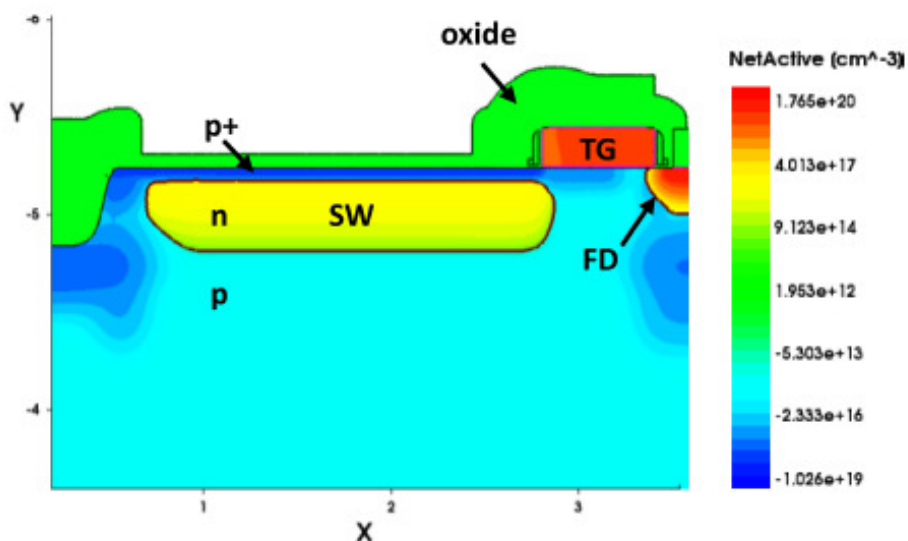


- **Average signal should be 2000-4000 e- (Landau-distributed)**
 - Beware of lower side tail and charge sharing
 - Many real signals will be smaller than this
- **As the CVF increases reset noise becomes small**
 - 16 e- RMS for 100 $\mu\text{V}/\text{e-}$ sense node
 - Correlated double sampling (CDS) still required for suppression of external interference, crosstalk, supply variations, etc.
- **Transistor noise (white and $1/f$) adds another ~ 10 e- RMS**
- **Very high SNR required**
 - Low amplification
 - Threshold for MIP detection should be large, e.g. $> 15\sigma$
 - Even 10σ threshold in a 30 Gpix system would produce 1.4 million fake hits

Pinned Photodiode (PPD)



- Also known as 4T pixel
- Widely used in imaging CMOS sensors with excellent performance
 - Noise could be $<1 e^-$
 - CDS comes naturally
 - Fast enough for HD video
- Not used in HEP (yet)



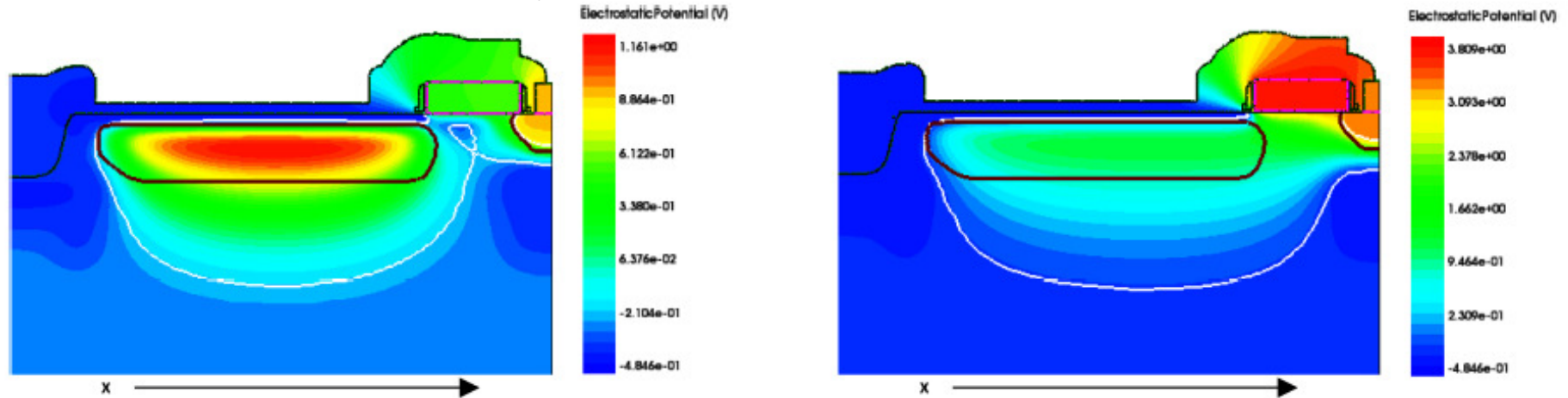
Eric Fossum, IEEE Journal of the Electron Devices Society (2014)



PPD Operation



Eric Fossum, IEEE Journal of the Electron Devices Society (2014)

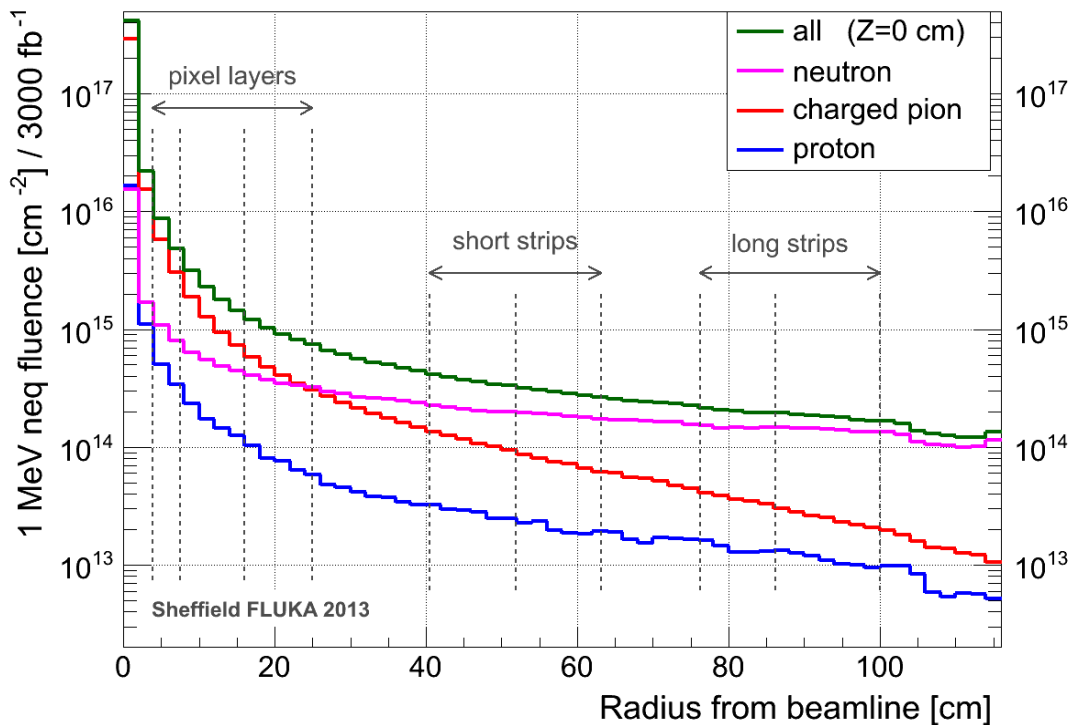


- Similar charge transfer happens in CCDs, but here without much electric field
- Charge transfer is slow (few μs)
 - Not a problem for an integrating tracker
- Photogate collection also possible – higher dark current, but charge transfer could be much faster
- Large pixels (50 μm) are a solvable challenge (common interests with X-ray detection)
- Full depletion possible too
- Large PPD pixel enabling integrating tracker could be a very strong proposition

Similar Technology for HL-LHC?



ATLAS Inner Tracker Fluences at the HL-LHC



- Synergies with HL-LHC could help fund detector development for ILC
- However, the radiation environment is much harsher: neutron fluence 10^{14} cm^{-2} is predicted
 - For ILC it is $5 \times 10^9 \text{ cm}^{-2}$
- Full depletion for prompt charge collection is a must, unlike for ILC
- Integrating tracker will not work for LHC, single bunch timing required
 - Power will be higher
- How to get LHC support (funding) for this?

Conclusions



- **Unique features of the integrating SPT**
 - Low mass enabled by low power dissipation
 - Charge transfer from a large diode to a small sense node
 - High sensitivity required to reduce power consumption
 - Binary readout
- **Challenges to work on:**
 - **Much more detailed study required on pixel and sensor architectures**
 - Pattern recognition with different degrees of integration to be proven
 - Mechanical support structure
- **An opportunity for international leadership by UK institutions**
- **I have now a 1-year project to develop fully depleted PPD pixels – large overlap with SPT**
- **Could be seeking support from CERN for HL-LHC**